

Substitute for form 1449A/B/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Application Number	Not Yet Assigned
		Filing Date	Concurrently Herewith
		First Named Inventor	Domenico LA FORGIA
		Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
		Attorney Docket Number	18628-232562
Sheet	1	of	1

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA	US-4,796,590 A	01-10-1989	DEGOBERT et al.	
	AB	US-4,614,961 A	09-30-1986	KHAN et al.	
	AC	US-5,278,435 A	01-11-1994	VAN HOVE et al.	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²	
	CA	MORKOC, H., "Potential applications of III-V nitride semiconductors", Materials Science and Engineering, vol. 43, no. 1-3, pages 137-146 (1994).		
	CB	MORKOC, H., ET AL., "GaN-based modulation doped FETs and UV detectors", Solid-State Electronics, vol. 46, no. 2, pages 157-202 (February 2002).		
	CC	POTI, et al., "High responsivity GaN-based UV detectors", Electronics Letters, vol. 39, no. 24, pages 1747-1749 (November 27, 2003).		
	CD	HENINI, M., "III-V nitrides for electronic and UV applications", III Vs Review, vol. 12, no. 5, pages 28, 30-32 (September 1999).		
	CE	STRITE, S., ET AL., "Progress and prospects for GaN and the III-V nitride semiconductors", Thin Solid Films, vol. 231, no. 1/2, pages 197-210 (August 25, 1993).		
	CF	STRITE, S., ET AL., "GaN, AlN, and InN: A Review", Journal Of Vacuum Science and Technology, vol. 10, no. 4, pages 1237-1266 (July 1992).		
	CG	SCHERER, A., ET AL., "InGaAsP photonic band gap crystal membrane microresonators", Journal Of Vacuum Science & Technology, vol. 16, no. 6, pages 3906-3910 (November 1998).		
	CH	MONROY, E., ET AL., "AlGaN-based UV photodetectors", Journal of Crystal Growth, vol. 230, no. 3-4, pages 537-543 (September 2001).		
	CI	DE VITTORIO, M., ET AL., "High temperature characterization of GaN-based photodetectors", Sensors and Actuators, vol. 113, no. 3, pages 329-333 (June 9, 2004).		

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Examiner Signature	/Arnold Castro/	Date Considered	09/13/2008
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ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /A.C./